



Suite 301, One Westlakes, Berwyn
P.O. Box 980
Valley Forge, PA 19482-0980
Phone: 610-407-0700
Fax: 610-407-0701

Nemours Building
1007 Orange Street, Suite 1100
P.O. Box 1596
Wilmington, DE 19899
Phone: 302-778-2500
Fax: 302-778-2600

Suite 265
Commerce Corporate Center
5100 Tilghman Street
Allentown, PA 18104
Phone: 610-530-8100
Fax: 610-530-8200

www.ratnerprestia.com

FACSIMILE COVER SHEET

DATE: September 24, 2003 OUR REF.: YAO-3950US and YAO-3950US2
TIME: YOUR REF.: 09/103,873 and 10/170,168

TO:	Examiner Jose R. Diaz
COMPANY:	United States Patent and Trademark Office
FROM:	Lawrence E. Ashery
FAX TELEPHONE:	(703) 308-7722 / (703) 746-3891
OFFICE TELEPHONE:	(703) 308-6078
TITLE OF DOCUMENT:	Draft Amendment for Review Only

Total Number of Pages: 11 *(including this form)*

COMMENTS

CONFIDENTIAL AND PRIVILEGED ATTORNEY/CLIENT INFORMATION

This facsimile transmission (and/or documents accompanying it) may contain attorney/client privileged communications and confidential business information that is intended for use only by the individual or company to whom it is addressed. Disclosure, interception, copying or any other use of this transmission by anyone other than any intended recipient is prohibited. If you receive this transmission by mistake, please notify the sender.

Please notify us immediately if you have not received the number of pages indicated above.

**DRAFT - FOR EXAMINER REVIEW ONLY
NOT FOR FILING**

Attorney Docket No. YAO-3950
PATENT

In re Application of : Group Art Unit: 2815
Yoshihisa Nagano et al. : Examiner: Jose R. Diaz
Serial No.: 09/103,873 :
Filed: June 24, 1998 :
For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

AMENDMENT UNDER 37 C.F.R. § 1.111

IN THE CLAIMS:

Please amend claims 1 and 32 as follows, and add claim 35:

1. (Currently amended) A semiconductor device, comprising:
a capacitor provided on supporting substrate [having an integrated circuit thereon] and including a lower electrode, a dielectric film, and an upper electrode, said dielectric film being formed from [either a dielectric material having a high dielectric constant or] a ferroelectric material;
a first interlayer insulating film provided so as to [directly] cover the capacitor;
a first interconnect selectively provided on the first interlayer insulating film and electrically connected to [the integrated circuit and] the capacitor through a first contact hole formed in the first interlayer insulating film;